# **Graphene Plasmonics**



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### The plasmon life cycle



# Graphene

A flat monolayer of carbon atoms tightly packed into a 2-dimensional honeycomb lattice





Castro Neto et. al, Rev. Mod. Phys. 2009



Das Sarma et. al, Rev. Mod. Phys. 2011

- High Mobility: 10000 cm<sup>2</sup>V<sup>-1</sup>s<sup>-1</sup>
- Zero band gap semiconductor
- Poor absorption in visible range
- Improve graphene device optical properties in visible and NIR
- Study graphene semi-metal properties in mid- or far- infrared

# Outline

Graphene-antenna sandwich
photodetector

 Doping graphene with plasmonic hot electrons

- Graphene nanostructures
  - nanodisk
  - nanoring





### **Graphene Photodetector**



E.J.Lee et.al. *Nature Nano.*,**3**, 488 (2008)



F.Xia et.al. Nano Lett.,9,1039 (2009)





X. Duan et.al. *Nature Comm.*,**2**, 579 (2011)

E.J.Lee et.al. Nature Comm., 2, 458 (2011)



#### Transfer a graphene monolayer onto a SiO<sub>2</sub>/Si substrate



#### Deposit the source-drain electrodes on the graphene



#### Fabricate heptamer array using two-step E-beam lithography



Transfer a second graphene monolayer onto the structure to form a sandwich device

### Sandwich Device Characterization

#### Optical image of the device



Dimer

Heptamer Nonamer

Second graphene on the top is used to capture the hot electrons from the whole *k*-space !

#### Raman mapping



### **Photocurrent Detection**



#### **Simulated Absorption Cross Section**



#### **Strong Electric-field Enhancement**



### **Polarization Dependence**



By choosing a different geometry, we can make either polarization dependent or independent photodectector

### Gate Voltage Control



By tuning the gate voltage from -40 to +40 V, we can actively control the photocurrent

### Gate Voltage Control

Source Electrode



Surface Potential Diagram



### **Selective Resonance Detection**



- Realize the tuning of resonance wavelength from visible to NIR
- Have a good agreement between the simulation and experiment

### Internal Quantum Efficiency



# Summary: graphene photodetector

#### Sandwich photodetector:

Fabricate antenna between two monolayer graphene, maximize signal from the whole *k*-space



#### Enhancement:

800% photocurrent enhancement, 20% internal quantum efficiency!

**Controllable:** polarization, size, resonance frequency (visible to near infrared), gate voltage tuning





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Nonamer

## Hole doping graphene



*p*-type doping graphene with quantum dots

Hole injection!

Can we realize *n*-type doping graphene by plasmonic hot electrons?

F. Koppens et.al. Nature Nano. 7,363 (2012)

#### **Graphene-Antenna Device**



<u>SEM</u> image for the nonamer fabricated on graphene using E-beam lithography



#### **Electrical Transport Characteristic**

at a source-drain bias of 1 mV Inset: *I-V* plots for various gate voltages  $V_G$  from 0 to 60V

# Dirac point shift with absorption



• Electrical transport characteristic ( $I-V_G$  curves) of the nonamer antennagraphene phototransistor

### Dirac point shift with absorption



The recorded Dirac point shift  $\Delta V = |V - V'|$  is proportional to the nonamer absorption cross-section  $\Delta V \propto \sigma_{abs}$ 

$$E_F = \hbar v_F \sqrt{\pi C_g (V_g - V_D) / eA}$$

### Dirac point shift with absorption



- Dependence of E<sub>F</sub> with photogenerated carrier density change
- Dependence of Source-drain current on photogenerated E<sub>F</sub> change

Z. Fang, F. Koppens, et. al. ACS Nano

### Antenna size control

Constant laser wavelength (785 nm) and power 14 **Disk Diameter** 100 ----- 230 nm Absorption Cross-section (a.u.) 12 -- 190 nm Source Drain Current (nA) 170 nm 80 Without Lase 10 -∆ V(V) 60 8-40 6 20 Dirac point shift 240 160 200 260 10 20 30 40 50 180 220 280 60 Gate Voltage (V) Disk Size (nm)

- *I-V<sub>G</sub>* curves for different sized nonamer array
- Dirac point shift data and the fitting curve simulated from structure absorption

### Hot electron recombination and scattering



Scattering Process

#### **Recombination:**

The internal electrostatic field drives a portion of the electrons back to the antenna

#### **Scattering:**

Injected hot electrons with the excessive electrons in graphene induced by Coloumbic interactions

#### **Doping timescale:**

estimated as  $10^{-6}$  s for the case  $\Delta V = 4V$ (under 5 µW incident laser power)

Z. Fang, F. Koppens, et. al. ACS Nano

# **Optical Induced Circuitry**



# Optical Induced graphene *p-n* junction

Optical Induced graphene *n-p-n* transistor

# Summery: hot electron doping graphene

#### Plasmonic hot electron doping graphene:

Different incident laser, antenna size, and incident laser power

#### Nonlinear saturating trend:

Hot electron recombination in Au antenna, and electron scattering in graphene

#### Time scale:

Hot electron doping  $(10^{-6} s)$  is much faster then *p*-type doping by using quantum dots

#### **Optical Induced Circuitry:**

*p-n* junction;

*n-p-n* transistor



# Outline

 Antenna-enhanced graphene sandwich photodetector

Plasmonic hot electrons doping graphene

- Graphene Nanostructures
  - nanodisk
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### Graphene nanodisk: plasmonic dipolar mode



$$\alpha(\omega) = \frac{3c^3}{4\omega^3} \frac{\kappa_r}{\omega_p - \omega - i\kappa/2}$$
$$\sigma^{\text{ext}}(\omega) = \frac{4\pi\omega}{c} \operatorname{Im}\{\alpha\} \approx \frac{3\lambda^2}{2\pi} \frac{\kappa_r}{\kappa}, \qquad \kappa_r \ll \kappa$$



## **Device Schematic**



Start with SiO<sub>2</sub> substrate



Deposit ITO layer



Transfer Graphene Monolayer



Pattern graphene with nanodisk array



Spin-coating lon gel





#### Graphene Nanodisk (D=50 nm) and Nanohole Array

Graphene Nanodisks

**Graphene Nanoholes** 



Center to center distance: 120 nm  $SiO_2$  thickness: 285 nm ITO thickness: 50 nm Ion gel thickness: 100 nm

Center to center distance: 250 nm

We can see the graphene wrinkle

Z. Fang, S. Thongrattanasiri, J. Garcia de Abajo, et. al. In preparation

#### Graphene nanodisk plasmon dipolar mode



Z. Fang, S. Thongrattanasiri, J. Garcia de Abajo, et. al. In preparation

#### Graphene nanodisk size control



Detected by using FTIR: Normal incidence

SiO2 thickness: 285 nm Ion gel thickness: 100 nm Graphene disk diameter: 50 to 190 nm

Z. Fang, S. Thongrattanasiri, J. Garcia de Abajo, et. al. In preparation

Extinction (a.u.)

#### Plasmon hybridization for metallic nanorings



E. Prodan, et al, Science, 419, 2003

#### **Theoretical Prediction**



S. Thongrattanasiri, J. Garcia de Abajo, Calculation

#### **Graphene Nanoring Structure**



# Conclusion

- Graphene-antenna photodetector
  - Sandwich structure
  - high enhancement in visible and NIR
  - High controllable device
- Plasmonic hot electrons doping graphene
  - Incident laser wavelength, power, antenna size
  - Hot electron recombination and further scattering
  - Doping time scale (10 μs)
- Graphene nanostructure
  - Nanodisk plasmonic dipoler resonance
  - Tuning with disk size and Fermi energy
  - Nanoring plasmonic bonding and anti-bonding modes





